

FEATURES

n **HIGH POWER**

P1dB=42.0dBm at 10.7GHz to 11.7GHz

n **HIGH GAIN**

G1dB=7.0dB at 10.7GHz to 11.7GHz

n **BROAD BAND INTERNALLY MATCHED FET**

n **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 9V f = 11.7 to 12.7GHz	dBm	41.0	42.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.0	7.0	—
Drain Current	IDS1		A	—	4.5	5.5
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	31	—
3 rd Order Intermodulation Distortion	IM3	Two-tone Test Po=30.0 dBm (Single Carrier Level)	dBc	-42	-45	—
Drain Current	IDS2		A	—	4.5	5.5
Channel Temperature Rise	ΔTch		°C	—	—	100
		(VDS X IDS + Pin – P1dB) X Rth(c-c)				

Recommended gate resistance(Rg) : Rg= 100 W(MAX.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

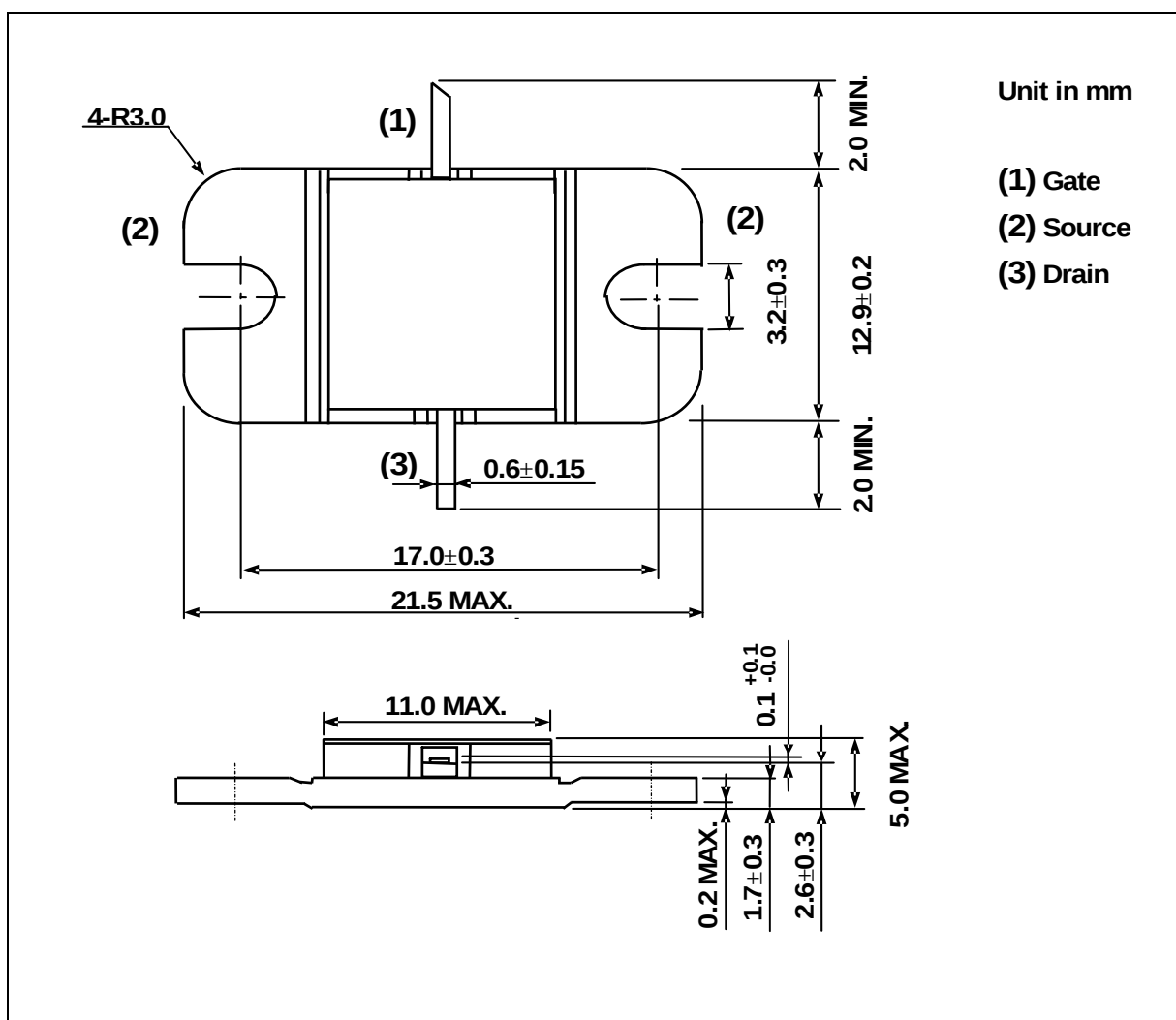
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	mS	—	3000	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	11.5
Gate-Source Breakdown Voltage	VGSO	IGS= -145μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

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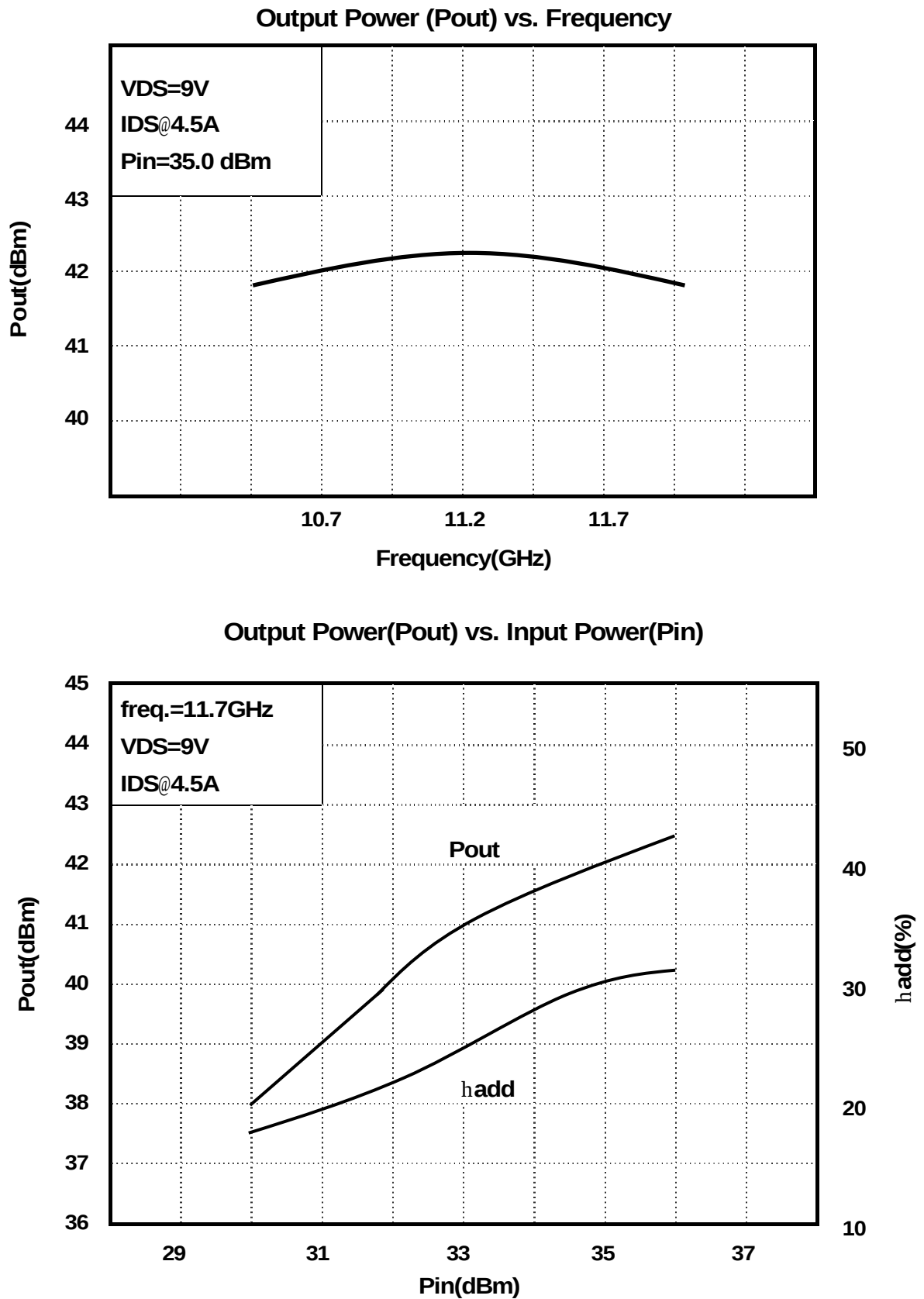
ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

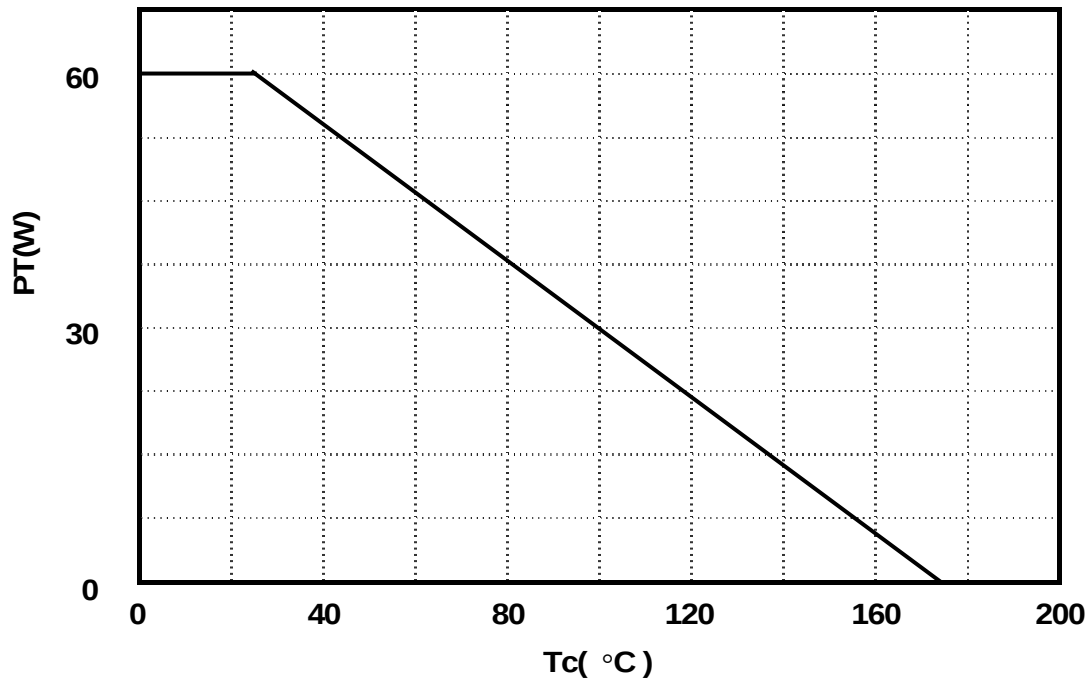
CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	11.5
Total Power Dissipation (T _c = 25 °C)	P _T	W	60.0
Channel Temperature	T _{ch}	°C	175
Storage	T _{stg}	°C	-65 ~ +175

PACKAGE OUTLINE (2-11C1B)**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCE



Power Dissipation(PT) vs. Case Temperature(Tc)**IM3 vs. Output Power Characteristics**